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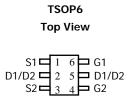
Dual N-Channel MOSFET

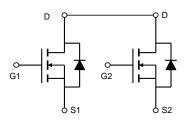
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
20	0.018 at V _{GS} = 4.5 V	5.6		
	0.023 at V _{GS} = 2.5 V	4.5		

FEATURES

- DT-Trench Power MOSFET
- 100 % UIS Tested
- + 100 % R_g Tested







ABSOLUTE MAXIMUM RATINGS T	A = 25 °C, unles	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Droin Current /T 150 °C)	T _A = 25 °C	- I _D	5.6	4.2	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		4.5	2.5	
Pulsed Drain Current		I _{DM}	30		A
Continuous Source Current (Diode Conduction) ^a		۱ _S	1.5	1.0	
	T _A = 25 °C	- P _D	1.5	1.0	w
Maximum Power Dissipation ^a	T _A = 70 °C		0.96	0.64	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Maximum handling to Ambianta	t ≤ 10 s	R _{thJA}	72	83	
Maximum Junction-to-Ambient ^a	Steady State		100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State		55	70	

Notes:

a. Surface Mounted on FR4 board, $t \leq$ 10 s.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.6		1.6	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 4.5 V$			± 200	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1	۵	
		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			25	μA	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \leq 5$ V, V_{GS} = 4.5 V	30			А	
Drain-Source On-State Resistance ^b	Б	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$	0.018 0.02		0.022		
	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 3.5 \text{ A}$		0.023	0.026	Ω	
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$		30		S	
Diode Forward Voltage ^b	V _{SD}	$I_{S} = 1.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.71	1.2	V	
Dynamic ^a	• • • •		•				
Total Gate Charge	Qg			12	18		
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	Q _{gd}			3.6			
Turn-On Delay Time	t _{d(on)}			245	365		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495	1	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		860	1300	ns	
Fall Time	t _f			510	765		

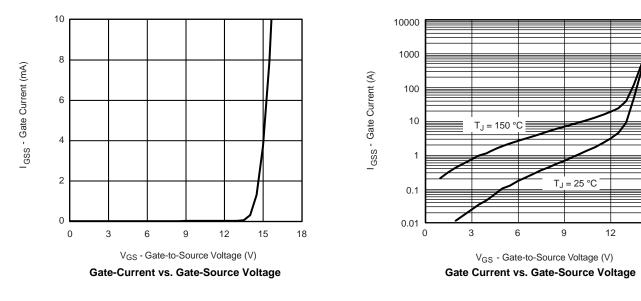
Notes:

a. For design aid only; not subject to production testing.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



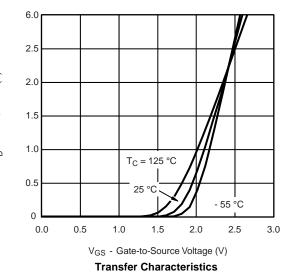


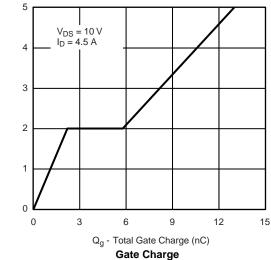
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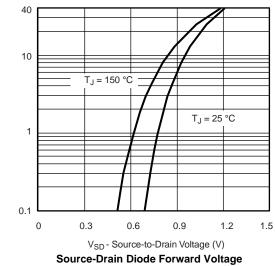
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6.0 V_{GS} = 5 thru 3 V 2.5 V 4.5 2.5 I_D - Drain Current (A) I_D - Drain Current (A) 2.0 2.0 1.5 1.5 1.0 1.0 2 V 0.5 0.5 0 0 0 2 3 4 5 0.0 1 V_{DS} - Drain-to-Source Voltage (V) **Output Characteristics** 0.06 5 V_{GS} - Gate-to-Source Voltage (V) 0.05 4 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - On-Resistance (Ω) 0.04 3 0.03 2 V_{GS} = 2.5 V $V_{GS} = 4.5 V$ 0.02 1 0 0.01 0 10 15 30 0 5 20 25 I_D - Drain Current (A) **On-Resistance vs. Drain Current** 0.05 40 $V_{GS} = 4.5 V$ $I_D = 4.5 A$ 0.04 10 R_{DS(on)} - On-Resistance Is - Source Current (A) (Normalized) 0.03 0.02 1 0.01 0 0.1 - 50 - 25 0 25 50 75 100 125 150 0 T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature



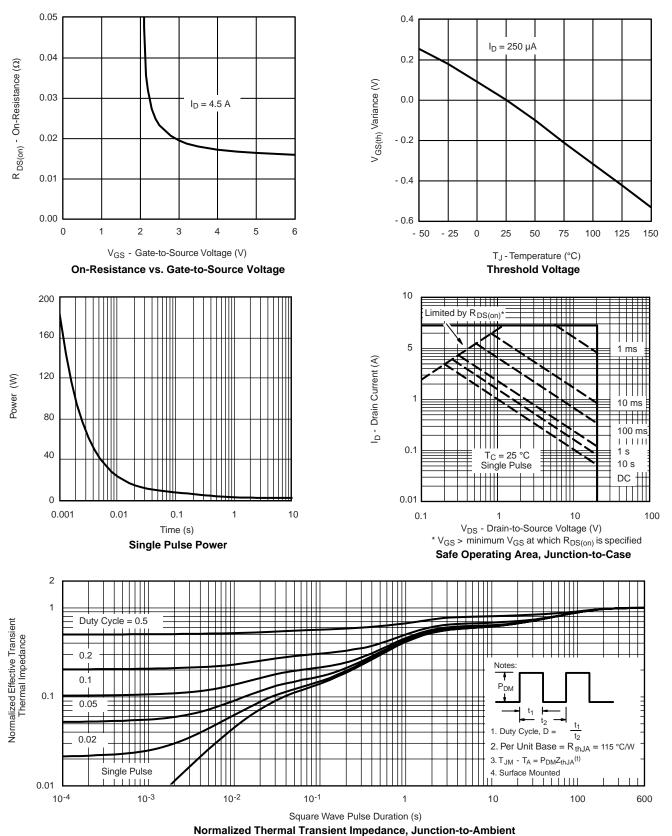




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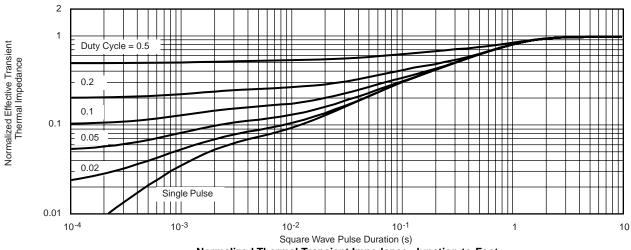






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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot



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